



## NTE5650 thru NTE5653 TRIAC – 100V<sub>RM</sub>, 2.5A

### Description:

The NTE5650 through NTE5653 sensitive gate TRIACs are designed to be driven directly with IC and MOS devices. These devices features a void-free glass passivated chip and are hermetically sealed in TO-5 outline cans.

The NTE5650 through NTE5653 are bi-directional triode thyristors and may be switched from off-state to conduction for either polarity of applied voltage with positive or negative gate-trigger current and are designed for control applications in lighting, heating, cooling and static switching relays.

### Absolute Maximum Ratings:

Repetitive Peak Off-State Voltage ( $T_J = +90^\circ\text{C}$ , Gate Open, Note 1),  $V_{\text{DROM}}$

NTE5650 .....	100V
NTE5651 .....	200V
NTE5652 .....	400V
NTE5653 .....	600V

RMS On-State Current ( $T_C = +75^\circ\text{C}$  and Conduction Angle of 360°),  $I_T(\text{RMS})$  ..... 3A

Peak Surge (Non-Repetitive) On-State Current (One-Cycleat 50Hz or 60Hz),  $I_{\text{TSM}}$  ..... 30A

Peak Gate-Trigger Current (3μsec, Max.),  $I_{\text{GTM}}$  ..... 1A

Peak Gate-Power Dissipation ( $I_{\text{GT}} \leq I_{\text{GTM}}$  for 3μsec. Max.),  $P_{\text{GM}}$  ..... 20W

Average Gate-Power Dissipation,  $P_{\text{G(AV)}}$  ..... 0.2W

Operating Temperature Range ( $T_C$ ),  $T_{\text{opr}}$  .....  $-40^\circ$  to  $+90^\circ\text{C}$

Storage Temperature Range,  $T_{\text{stg}}$  .....  $-40^\circ$  to  $+150^\circ\text{C}$

Typical Thermal Resistance, Junction-to-Case,  $R_{\text{thJC}}$  .....  $4^\circ\text{C/W}$

Note 1. All values apply in either direction.

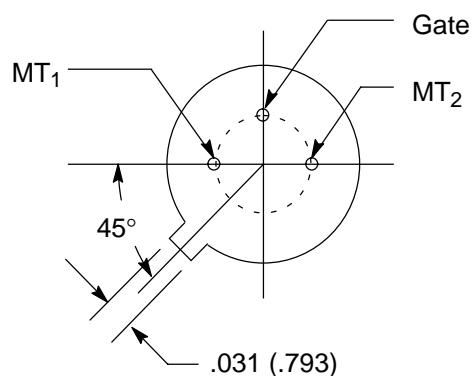
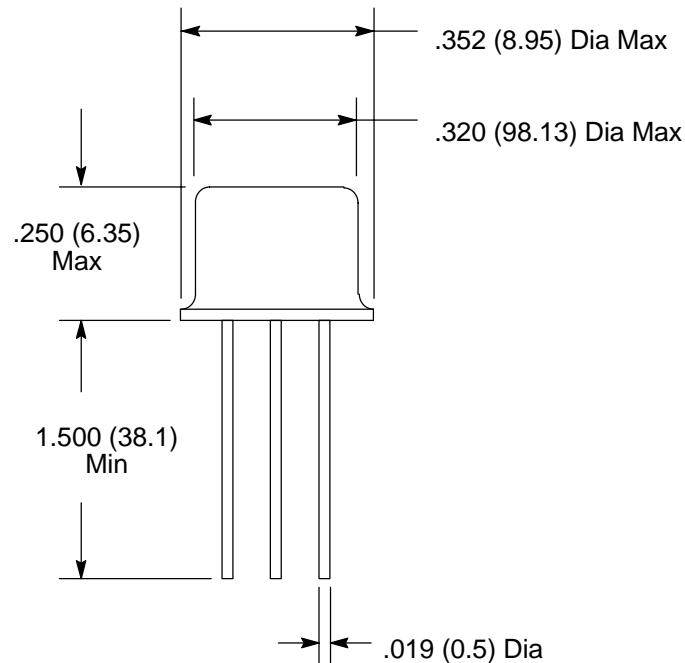
### Electrical Characteristics: (At Maximum Ratings & Specified Case Temperature)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Peak Off-State Current	$I_{\text{DROM}}$	$T_J = +90^\circ\text{C}$ , $V_{\text{DROM}} = \text{Max Rating}$ , Gate Open, Note 1	—	—	0.75	mA
Maximum On-State Voltage	$V_{\text{TM}}$	$T_C = +25^\circ\text{C}$ , $i_T = 5\text{A}$ (Peak), Note 1	—	—	1.85	V
DC Holding Current	$I_{\text{HO}}$	$T_C = +25^\circ\text{C}$ , Gate Open	—	—	5	mA
Critical Rate-of-Rise of Off-State Voltage	Critical $\frac{dv}{dt}$	$T_C = +90^\circ\text{C}$ , $v_D = V_{\text{DROM}}$ , Gate Open, Note 1	—	3	—	$\text{V}/\mu\text{s}$
DC Gate-Trigger Current $MT_2 (+)$ Gate (+), $MT_2 (-)$ Gate (-)	$I_{\text{GT}}$	$T_C = +25^\circ\text{C}$ , $v_D = 6\text{V}$ , $R_L = 39\Omega$	—	—	3	mA
$MT_2 (+)$ Gate (-), $MT_2 (-)$ Gate (+)						

Note 1. All values apply in either direction.

**Electrical Characteristics (Cont'd):** (At Maximum Ratings & Specified Case Temperature)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
DC Gate Trigger Voltage	$V_{GT}$	$T_C = +25^\circ\text{C}$ , $v_D = 6\text{V}$ , $R_L = 39\Omega$	—	—	2.2	V
Gate-Controlled Turn-On Time	$t_{gt}$	$T_C = +25^\circ\text{C}$ , $v_D = V_{DROM}$ , $I_{GT} = 80\text{mA}$ , $t_r = 0.1\mu\text{s}$ , $i_T = 10\text{A}$ (Peak)	—	2.2	—	$\mu\text{s}$
Fusing Current (For TRIAC Protection)	$I^2t$	$T = 1.25$ to $10\text{ms}$	—	—	3	$\text{A}^2\text{s}$



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